

Silicon NPN Power Transistors

2SC1875

DESCRIPTION

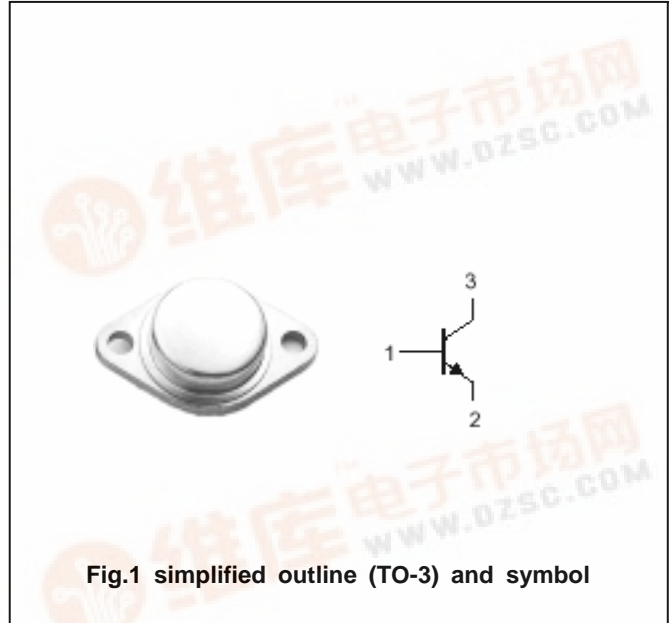
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Designed for use in large screen color deflection circuits

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3.5	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		1.0	A
P _C	Collector power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction case	2.5	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	500			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5A; I _B =0.6A			10	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.5A; I _B =0.6A			1.2	V
I _{CES}	Collector cut-off current	V _{CE} =1500V; V _{BE} =0			1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			20	μA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =10V	10		35	
h _{FE-2}	DC current gain	I _C =2A ; V _{CE} =10V	5		25	
t _s	Storage time	I _C =2.5A ; I _{B1} =-I _{B2} =0.6A P _w =20 μs		10		μs
t _f	Fall time			1.0		μs

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PACKAGE OUTLINE

